



YOUSHANG SEMICONDUCTOR

**设计研发新型功率器件**

**各类小信号开关**

**中低压及高压大电流等场效应管**

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## Features

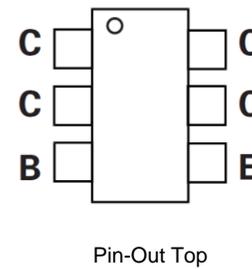
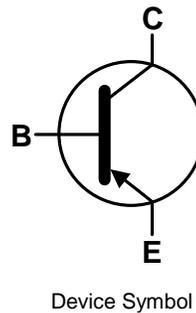
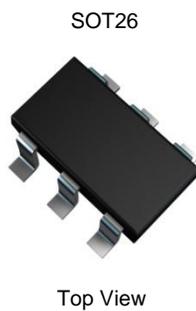
- $BV_{CEO} > -20V$
- $I_C = -3.5A$  Continuous Collector Current
- $I_{CM} = -10A$  Peak Pulse Current
- $R_{CE(sat)} = 75m\Omega$  for a Low Equivalent On-Resistance
- Low Saturation Voltage of  $<-130mV$  max @  $-1A$
- $h_{FE}$  Characterized up to  $-10A$  for High Current Gain Hold-Up

## Mechanical Data

- Case: SOT26
- Case Material: Molded Plastic, "Green" Molding Compound; UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – Matte Tin Plated Leads; Solderable per MIL-STD-202, Method 208 (E3)
- Weight: 0.015 grams (Approximate)

## Applications

- DC-DC Converters
- Power Management Functions
- Power Switches
- Motor Control



### Absolute Maximum Ratings

 (@ $T_A = +25^{\circ}\text{C}$ , unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	$V_{CBO}$	-25	V
Collector-Emitter Voltage	$V_{CEO}$	-20	V
Emitter-Base Voltage	$V_{EBO}$	-7.5	V
Base Current	$I_B$	-500	mA
Continuous Collector Current	$I_C$	-3.5	A
Peak Pulse Collector Current	$I_{CM}$	-10	A

### Thermal Characteristics

 (@ $T_A = +25^{\circ}\text{C}$ , unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation Linear Derating Factor	$P_D$	1.1	W
		8.8	
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	1.7	$\text{mW}/^{\circ}\text{C}$
		13.6	
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	113	$^{\circ}\text{C}/\text{W}$
		73	
Thermal Resistance, Junction to Lead	$R_{\theta JL}$	18.61	$^{\circ}\text{C}/\text{W}$
Operating and Storage Temperature Range	$T_J, T_{STG}$	-55 to +150	$^{\circ}\text{C}$

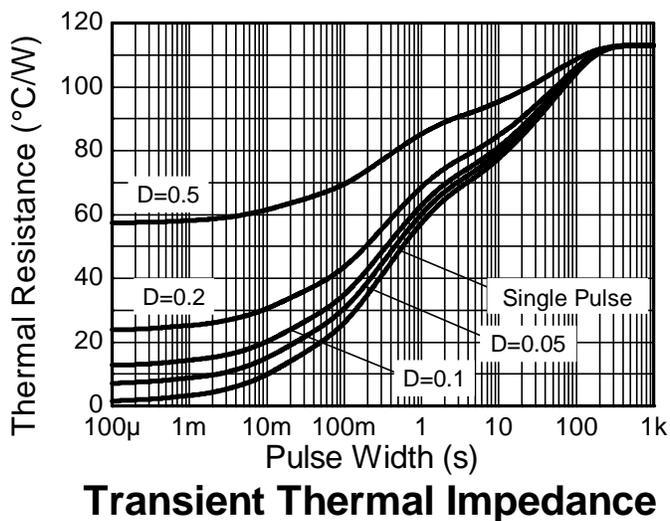
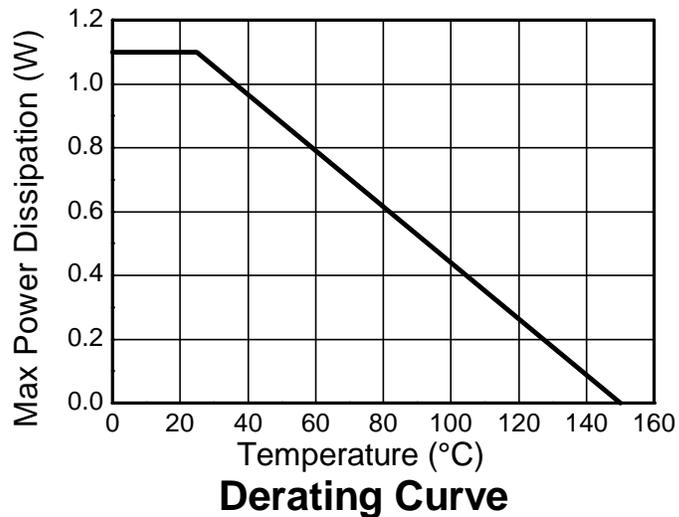
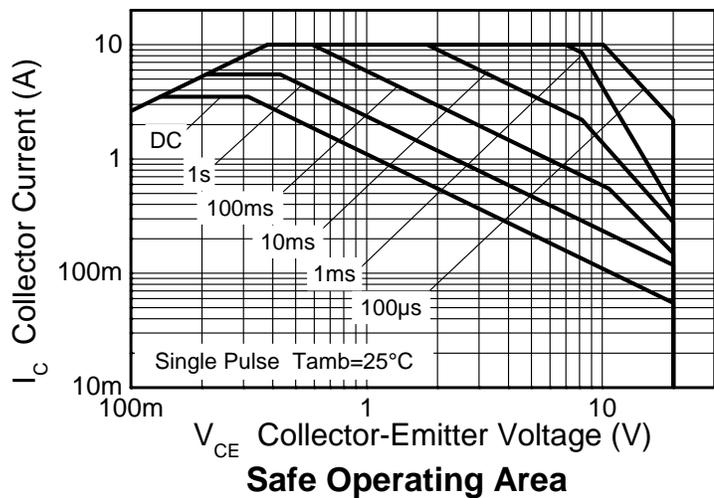
### ESD Ratings

 (Note 8)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	C

- Notes:
5. For a device mounted with collector leads on 25mm x 25mm 1oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.
  6. Same as Note 5, except the device is measured at  $t \leq 5$  seconds.
  7. Thermal resistance from junction to solder-point (at the end of the collector leads).
  8. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

**Thermal Characteristics and Derating Information**

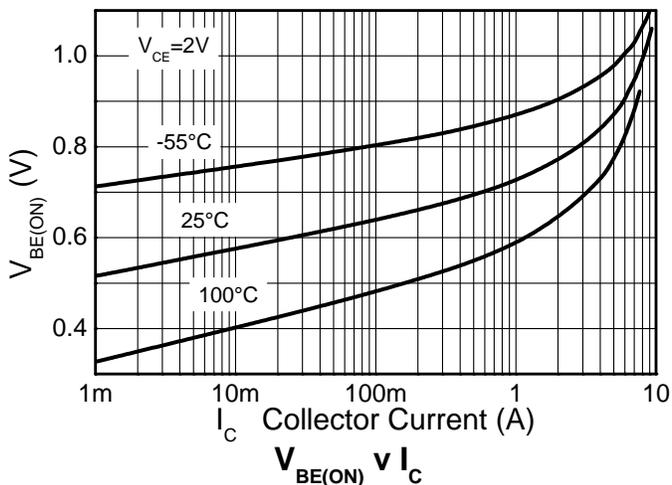
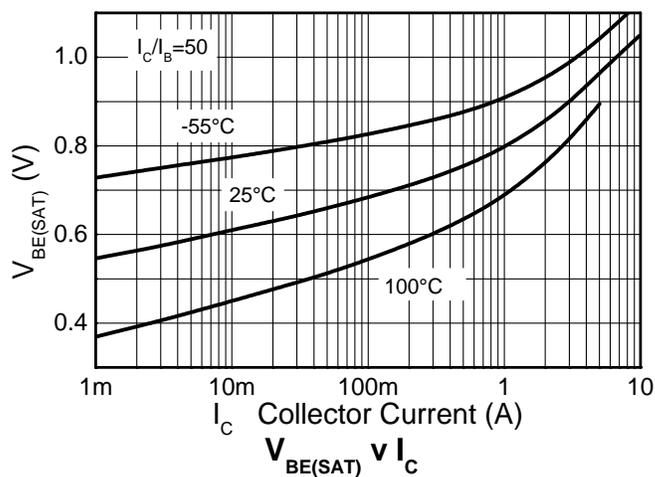
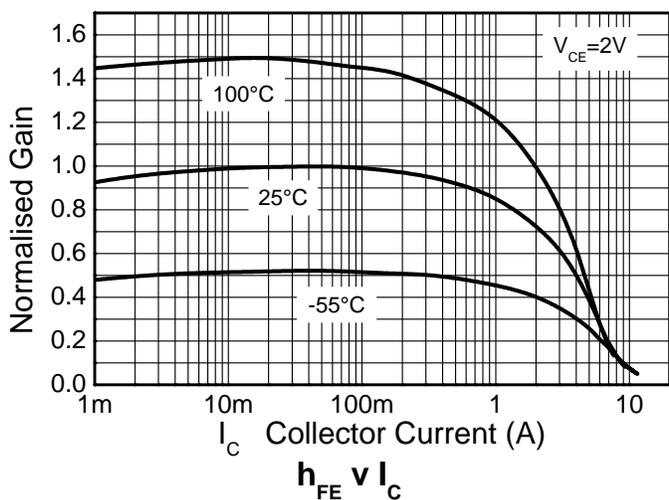
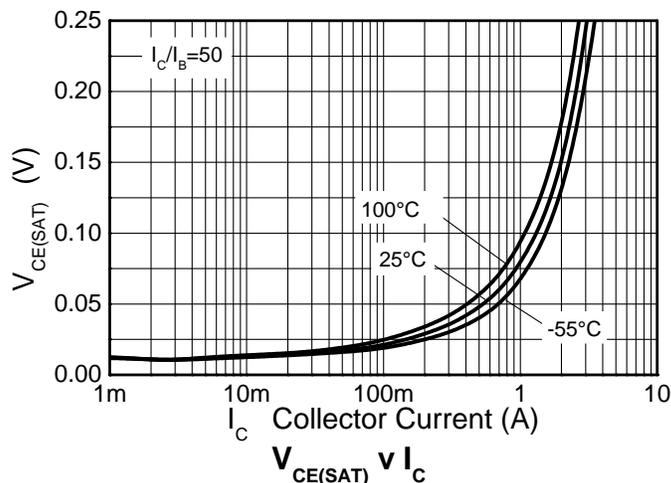
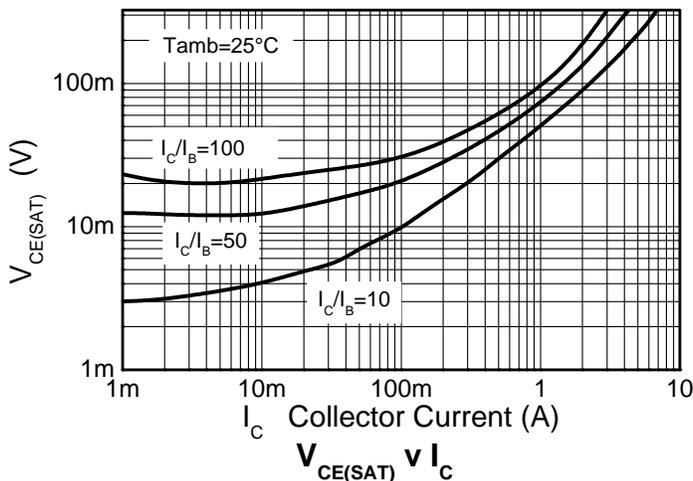


**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

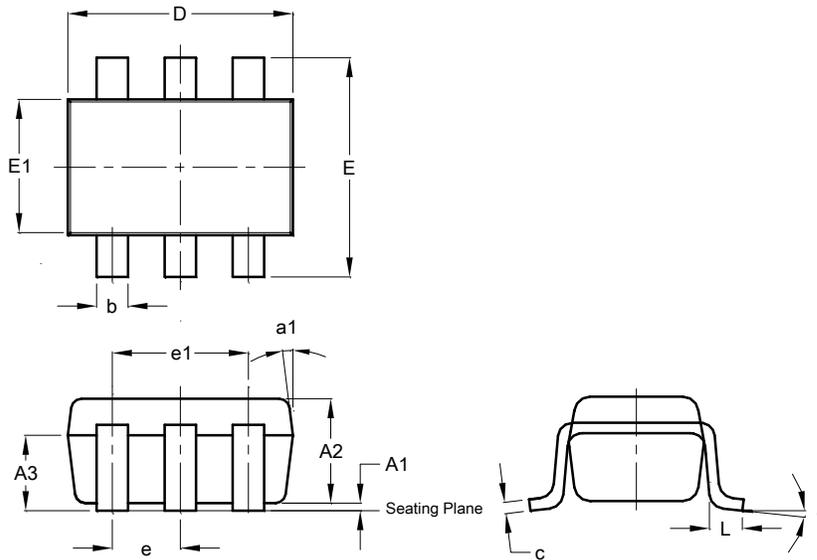
Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS</b>						
Collector-Base Breakdown Voltage	BV <sub>CB0</sub>	-25	-55	—	V	I <sub>C</sub> = -100μA
Collector-Emitter Breakdown Voltage (Note 9)	BV <sub>CEO</sub>	-20	-50	—	V	I <sub>C</sub> = -10mA
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	-7.5	-8.5	—	V	I <sub>E</sub> = -100μA
Collector-Base Cut-Off Current	I <sub>CB0</sub>	—	—	-100	nA	V <sub>CB</sub> = -20V
Emitter Cut-Off Current	I <sub>EBO</sub>	—	—	-100	nA	V <sub>EB</sub> = -6V
Collector-Emitter Cut-Off Current	I <sub>CES</sub>	—	—	-100	nA	V <sub>CES</sub> = -20V
<b>ON CHARACTERISTICS (Note 9)</b>						
DC Current Gain	h <sub>FE</sub>	300	500	—	—	I <sub>C</sub> = -10mA, V <sub>CE</sub> = -2V
		300	450	900	—	I <sub>C</sub> = -1A, V <sub>CE</sub> = -2V
		150	250	—	—	I <sub>C</sub> = -3.5A, V <sub>CE</sub> = -2V
		10	—	—	—	I <sub>C</sub> = -10A, V <sub>CE</sub> = -2V
Collector-Emitter Saturation Voltage	V <sub>CE(sat)</sub>	—	-10	-15	mV	I <sub>C</sub> = -100mA, I <sub>B</sub> = -10mA
		—	-100	-130		I <sub>C</sub> = -1A, I <sub>B</sub> = -10mA
		—	-165	-250		I <sub>C</sub> = -3.5A, I <sub>B</sub> = -350mA
Base-Emitter Saturation Voltage	V <sub>BE(sat)</sub>	—	—	-1.1	V	I <sub>C</sub> = -3.5A, I <sub>B</sub> = -350mA
Base-Emitter Turn-On Voltage	V <sub>BE(on)</sub>	—	—	-0.9	V	I <sub>C</sub> = -3.5A, V <sub>CE</sub> = -2V
<b>SMALL SIGNAL CHARACTERISTICS</b>						
Current Gain-Bandwidth Product	f <sub>T</sub>	—	90	—	MHz	V <sub>CE</sub> = -10V, I <sub>C</sub> = -50mA, f = 50MHz
Output Capacitance	C <sub>obo</sub>	—	62	—	pF	V <sub>CB</sub> = -10V, f = 1MHz
Turn-On Time	t <sub>(on)</sub>	—	95	—	ns	V <sub>CC</sub> = -10V, I <sub>C</sub> = -2A
Turn-Off Time	t <sub>(off)</sub>	—	395	—	ns	I <sub>B1</sub> = I <sub>B2</sub> = -40mA

Note: 9. Measured under pulsed conditions; pulse width ≤ 300μs, duty cycle ≤ 2%.

**Typical Electrical Characteristics** (@ $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

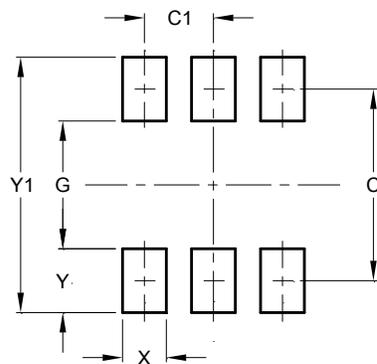


### Package Outline



SOT26			
Dim	Min	Max	Typ
A1	0.013	0.10	0.05
A2	1.00	1.30	1.10
A3	0.70	0.80	0.75
b	0.35	0.50	0.38
c	0.10	0.20	0.15
D	2.90	3.10	3.00
e	-	-	0.95
e1	-	-	1.90
E	2.70	3.00	2.80
E1	1.50	1.70	1.60
L	0.35	0.55	0.40
a	-	-	8°
a1	-	-	7°
All Dimensions in mm			

### Suggested Pad Layout



Dimensions	Value (in mm)
C	2.40
C1	0.95
G	1.60
X	0.55
Y	0.80
Y1	3.20